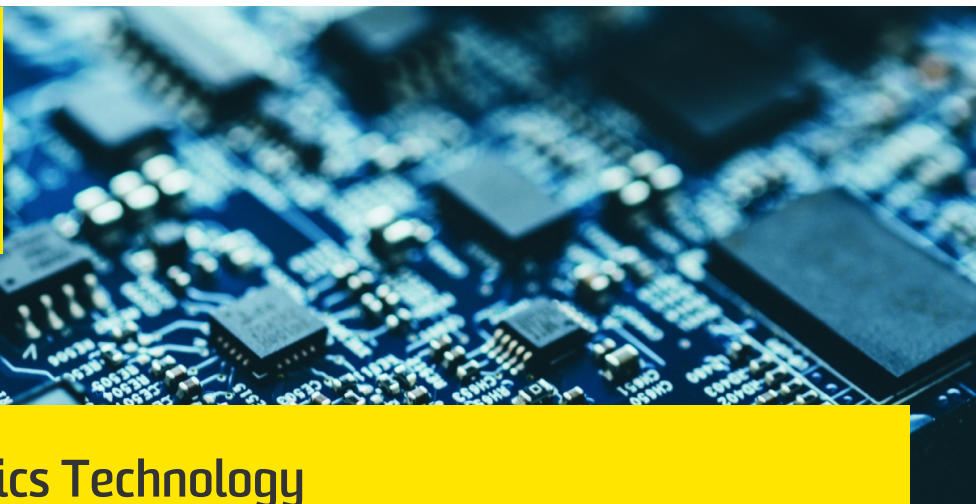




UNSW
SYDNEY



Oxide Nanoelectronics Technology

Oxide nano-electronic materials promise dramatic improvements in the performance and lifespan of electronic devices. Due to these superior properties, the materials have been implemented in radiation-hardened circuits for space applications, in an array of sensors and actuators, and within next-generation electronics such as ferroelectric memory.

Competitive advantage

- Pioneering research into conducting materials with nanoscale topological features
- Key skills in design of materials with sub-nanometer ion channels
- Advanced scanning probe microscopy including instrument development
- Demonstrated first domain wall electronics elements
- A leading publication and IP profile within this critical research field
- As a member of the Australian Research Centre (ARC) Centre of Excellence in future low-energy electronics technologies, this group has access to state-of-the-art nanoelectronics characterisation equipment.

Impact

- Potential use in reconfigurable electronics, ultralow energy technology, domain wall memory, radiation detectors, sub-nanometer ion channels, and radiation hardened electronics

Successful applications

- Domain wall memory, utilising magnetic oxides is approaching commercial implementation, team holds key IP in the field
- Characterisation of bespoke circuits for critical hardened electronics applications

Capabilities and facilities

- Specialised tools and expertise in materials synthesis using ultra-high vacuum technology and pulsed laser deposition
- State-of-the art scanning probe microscopy material characterisation techniques

Our partners

- US Office of Naval Research
- Intel Corporation
- Australian semiconductor manufacturers (Silanna, among others)

More Information

Professor Jan Seidel

School of Materials Science and Engineering

T: +61 (0) 2 9385 4442

E: jan.seidel@unsw.edu.au

UNSW Knowledge Exchange

knowledge.exchange@unsw.edu.au

www.capabilities.unsw.edu.au

+61 (2) 9385 5008